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Title of the experiment:

Determination of energy band gap of a semiconductor by Four probe method.

objective:

To determine the band gap of a semi and uctor by measuring the resistivity as a function of temperatural using four probe method.

equipment list:-

U spring loaded four probes

- & Germanium (semiconductor) crystal
- 3) oven (upto 150°C)
- 4 thermometer
- S constant current source
- 6 voltmeter and

Formula:

PCT) = Poemp (+ Eg)

6- Residual conductivity

Slope

YT

Eg-Band gap of the intrinsic semiconduction

K- Boltzman constant

T- absolute temperature

$$P=CF(\frac{\vee}{I}) \Rightarrow P=0.213\times(\frac{\vee}{I})$$

I - current passing through the semiconduly

v-measured voltage

Band Gap Energy:

m -> slope of the graph logePDS IT

Report: - K-> Boltzman constant = 8.617 × 10 Sev/k Temperature voltage Resistively 1/7 loge (CV) (p) (p1) S.NB 18.65 rm 3.33 2.91 0.303 300 79.69 vm 3.19 × 2.97 313 0.323 323 0.33) ×163 3.00 20.14 Mm 333 0.332 20.20 Am ×193 3.00 343 0.315 19.17 m 2.91 × 163 2.95 353 0.300 18-252m X103 2.90 363 0-213 13.5 3 VW 5.32 5.60

calculations:

dations:
$$T = 3.5 \times 10^{3}$$

0 bs1:-

$$651$$
:-
 $9 = 0.213 \times V = 0.213 \times \frac{0.303}{3.5 \times 16^3}$

obs2:

S2:

$$P = 0.213 + V = 0.213 \times 0.393 = 19.65 \text{ nm}$$

 $\frac{3.5 \times 10^{3}}{3.5 \times 10^{3}} = 19.65 \text{ nm}$

$$\rho = 0.213 \times \frac{V}{I} = 0.213 \times 0.33) = 20.14 \text{ Lm}$$

obsu:

Su:
$$\rho = 0.213 \times \frac{1}{2} = 0.213 \times 0.332 = 20.20 \text{ Lm}$$

$$\frac{55!}{P=0.2134V} = \frac{0.213\times0.315}{3.5\times10^{3}} = 19.17 \text{ Jm}$$

Obs6:

S6:

$$P = 0.213 + V = 0.213 + 0.300 = 18.25 \text{ nm}$$

 $3.5 + 10^{-3}$

Obs 7:

$$P = 0.213 \times V = \frac{0.213 \times 0.223}{3.5 \times 10^{-3}} = 13.57 \text{ nm}$$

From graph,

$$P(T) = Po exp(\frac{Eg}{2kT})$$

Result:

The band gap energy (Eg) of the germanium crystal is 0.64 eV